| L Number | Hits | Search Text | DB | Time stamp |
|----------|-------|-----------------------------------------------------------------------------------|------------------------|------------------|
| 1 | 0 | (flash near2 anneal\$3) near10 ((back or | USPAT; | 2004/08/21 20:54 |
| | | bottom) near5 (substrate or wafer)) | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | (51h2162)10 (impine62 | IBM_TDB | 2004/00/21 21.21 |
| 2 | 0 | (flash near2 anneal\$3) near10 (imping\$3 near5 (support near2 substrate)) | USPAT; US-PGPUB; | 2004/08/21 21:31 |
| | | nears (support nearz substrace); | EPO; JPO; | |
| | ļ | | DERWENT; | |
| | | | IBM TDB | |
| 3 | 0 | anneal\$3 near10 (imping\$3 near5 (support | USPAT; | 2004/08/21 21:32 |
| | ĺ | near2 substrate)) | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| 4 | 0 | annoaled same (impinated nearth (support | IBM_TDB USPAT; | 2004/08/21 21:32 |
| 4 | ١ | anneal\$3 same (imping\$3 near5 (support near2 substrate)) | US-PGPUB; | 2004/00/21 21:32 |
| | | Near 2 Substrace, | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM TDB | |
| 5 | 0 | anneal\$3 same (imping\$3 or though) near5 | USPĀT; | 2004/08/21 21:33 |
| | | (support near2 substrate) | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; IBM TDB | |
| 6 | 10 | anneal\$3 same ((imping\$3 or through) | USPAT; | 2004/08/21 21:35 |
| * | | near5 (support near2 substrate)) | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | • | DERWENT; | |
| | _ | | IBM_TDB | |
| 7 | 8 | (flash near2 anneal\$3 same ((imping\$3 or | USPAT; | 2004/08/21 21:35 |
| | | through) near5 substrate)) | US-PGPUB; | |
| | | | EPO; JPO; DERWENT; | |
| ľ | | | IBM TDB | |
| _ | 6192 | ((438/149) or (438/311) or (438/458) or | USPAT; | 2004/08/20 17:34 |
| | | (438/473) or (438/474) or (438/475) or | US-PGPUB; | |
| | | (438/477) or (438/479) or (438/480) or | EPO; JPO; | |
| | | (438/495) or (438/496) or (438/499) or | DERWENT; | |
| | | (438/406) or (438/508) or (438/509) or (438/514) or (438/787) or (438/788)).CCLS. | IBM_TDB | |
| _ | 17530 | (soi or (silicon near2 insulator) or sog | USPAT; | 2004/08/21 16:28 |
| | | or (silicon near2 quartz) or sof or | US-PGPUB; | |
| | | (silicon near2 foreign)) near3 (substrate | EPO; JPO; | |
| | | or wafer) | DERWENT; | |
| | | (,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,, | IBM_TDB | 0004/00/00 1= 1= |
| - | 0 | (((xe adj arc) near2 lamp) same anneal\$3) | USPAT; | 2004/08/20 17:48 |
| | | near10 ((support or second silicon or quartz or semiconductor)near2 substrate) | US-PGPUB; EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM TDB | |
| - | 0 | , (, ()+,++ | USPAT; | 2004/08/20 17:48 |
| | | same ((support or second silicon or quartz | US-PGPUB; | |
| | | or semiconductor)near2 substrate) | EPO; JPO; | |
| | | | DERWENT; IBM TDB | |
| _ | 0 | (((xe adj arc) near2 lamp) same anneal\$3) | USPAT; | 2004/08/20 17:49 |
| | | same ((support or second or silicon or | US-PGPUB; | |
| | | quartz or semiconductor) near2 substrate) | EPO; JPO; | |
| 1 | | | DERWENT; | |
| | ا م | | IBM_TDB | |
| - | 0 | , , , , , , , , , , , , , , , , , , , | USPAT; | 2004/08/20 17:49 |
| | | or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate | US-PGPUB; EPO; JPO; | |
| | | or wafer)) and ((((xe adj arc) near2 lamp) | DERWENT; | |
| | | same anneal\$3) and ((support or second or | IBM TDB | |
|] | | silicon or quartz or semiconductor) near2 | _ | |
| | | substrate)) | 1 | |

| 26 (((xe adj arc) near2 lamp) same anneal53 and ((support or second or silicon or quartz or semiconductor)near2 substrate) US-RCPUB CS-RCPUB CS-RC | | | | | |
|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------|---------|-----------------------------------------------|-----------|--------------------|
| Quartz of semiconductor)near2 substrate EPO, JFO; DERMENT; IEM TDB USPAT; DERMENT; IEM TDB | - | 26 | | | 2004/08/20 17:50 |
| Contents | | | | | |
| 188 TDS 1897T; | | | quartz or semiconductor/nearz substrate/ | | |
| S | | | | | |
| Or heat\$3) near10 (substrate or (support near2 substrate) SPO JPO JPO JERREBYT SPO JPO JPO JPO JPO JPO JPO JPO JPO JPO J | _ | 5 | (((xe adi arc) near2 lamp) same (anneal\$3 | | 2004/08/20 17:52 |
| near2 substrate) | | | | | 2001, 00, 20 2.102 |
| - 54 (((xe adj arc) near2 lamp) same (anneal33 or heat33)) - 0 ((soi or (silicon near2 insulator) or soq or (silicon near2 foreign)) near3 (substrate or wafer)) and ((((xe adj arc) near2 lamp) and (anneal53 or heat53)) | | | | | i |
| 1 | | 1 | , | | |
| Or heat\$3) Or heat\$3) Or heat\$3) Or heat\$3) | <u> </u> | | | | |
| Or heat\$3) Os-FGFUB; EPG, JPG; JPG; JPG; JPG; JPG; JPG; JPG; JPG; | _ | 54 | (((xe adj arc) near2 lamp) same (anneal\$3 | USPAT; | 2004/08/20 17:53 |
| - | | İ | | US-PGPUB; | |
| Compared | | | | EPO; JPO; | İ |
| 0 | | ļ | | DERWENT; | |
| or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer) and ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) (((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and ((soi or (silicon near2 lamp) defense) ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and ((soi or (silicon near2 lamp) defense) (((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and ((soi or (silicon near2 lamp) defense) ((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) ((((xe adj arc) near2 lamp) and (anneal\$3 or ((((xe adj arc) near2 foreign)) defense) ((((xe adj arc) near2 foreign)) defense) ((((xe adj arc) near2 foreign)) defense) ((((xe adj arc) near2 foreign)) defense) ((((xe adj arc) near2 foreign)) defense) ((((xe adj arc) near2 foreign)) defense) (((((xe adj arc) near2 foreign)) defense) (((((xe adj arc) near2 foreign)) defense) (((((xe adj arc) near2 foreign)) defense) ((((xe adj arc) near2 foreign)) defense) ((((xe adj arc) near2 foreign)) dear3 (substrate or wafer)) (((((xe adj arc) near2 foreign)) dear3 (substrate or wafer)) (((((xe adj arc) near2 foreign)) dear3 (substrate or wafer)) ((((xe adj arc) near2 foreign)) dear3 (substrate or wafer)) ((((xe adj arc) near2 foreign)) dear3 (substrate or wafer)) ((((xe adj arc) near2 foreign)) dear3 (substrate or wafer)) ((((xe adj arc) near2 foreign)) dear3 (substrate or wafer)) (((xe adj arc) near2 foreign)) dear3 (substrate or wafer)) (((xe adj arc) near2 foreign)) dear3 (substrate or wafer)) (((xe adj arc) near2 foreign)) dear3 (substrate or wafer)) (((xe adj arc) near2 foreign)) dear3 (substrate or wafer)) ((xe adj arc) near2 foreign)) dear3 ((xe) foreign) (xe) foreign | | | | | |
| (silicon near2 foreign) near3 (substrate or wafer) and ((((xe adj arc) near2 lamp) same (anneal\$3 or heat\$3)) | - | 0 | | USPAT; | 2004/08/20 17:53 |
| or wafer) and (((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) | | | | | |
| Same (anneal\$3 or heat\$3)) IM TDB (((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) Cond/08/20 18:03 | | | | | |
| - 206 (((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) - 0 ((((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and ((soi or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (438/473) or (438/479) or (438/48) or (438/480) or (438/480) or (438/495) or (438/496) or (438/480) or (438/514) or (438/787) or (438/783)) and ((soi or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 foreign)) near3 (substrate or wafer)) - 2450 ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) - 2450 ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) - ((soi or (silicon near2 insulator) or soq or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) - ((soi or (silicon near2 insulator) or soq or (silicon near2 foreign)) near3 (substrate or wafer) and (wafer near2 bond\$3) and ((((so adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and (((soi or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) and (((soi or (silicon near2 lamp) and (anneal\$3 or heat\$3)) and (((soi or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) and (((soi or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) and (((soi or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) and (((soi or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) and (((soi or (silicon near2 foreign)) near3 (substrate or wafer)) near3 (substrate or wafer)) near3 (substrate or wafer) near3 (substrate o | | | | | |
| - 0 ((((((xe adj arc) near2 lamp) and (anneal33 or heat\$31)) and ((soi or (silicon near2 lamp)) and (soi or (silicon near2 lamp)) and ((((438/449) or (438/449) or (438/449)) or (438/449) or (438/449) or (438/449) or (438/449) or (438/499) or (438/496) or (438/599) or (438 | | | | | |
| - 0 (((((((((((((((((((((((((((((((((((| - | 206 | 1 1 1 1 2 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 | | 2004/08/20 18:03 |
| - 0 (((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3))) and ((soi or (silicon near2 lamp) and (anneal\$3 or heat\$3))) and ((soi or (silicon near2 lamp) and (anneal\$3 or heat\$3))) and ((soi or (silicon near2 lamp) and (anneal\$3 or heat\$3))) and (((388/311) or (438/458) or (438/473) or (438/474) or (438/480) or (438/477) or (438/479) or (438/480) or (438/780) or | | | or heat\$3)) | | |
| TIM TDB | | | | | |
| O (((((xe adj arc) near2 lamp) and (anneal\$3 | | | | | |
| Or heat\$3) and ((soi or (silicon near2 insulator) or soq or (silicon near2) US-PGPUB; EPO; JPO; JPO; JPO; JPO; JPO; JPO; JPO; J | | _ | 111111111111111111111111111111111111111 | | 2004/00/00 17 50 |
| insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (((438/449) or (438/471) or (438/475) or (438/475) or (438/470) or (438/4796) or (438/4796) or (438/4799) or (438/4789).CCLS.) - 34 ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and ((soi or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) wafer near2 bond\$3 - 2450 (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) - 0 (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) and ((((xe adj arc) near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3)) and ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and (((soi or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3)) and (((soi or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3)) and (((soi or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3)) and ((((soi or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3)) and (((soi or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3)) and (((soi or (silicon near2 foreign)) near3 (substrate or between the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the following the | - | 0 | | | 2004/08/20 17:53 |
| quartz or sof or (silicon near2 foreign) near3 (substrate or wafer) and (((438/449) or (438/458) or (438/473) or (438/475) or (438/477) or (438/479) or (438/475) or (438/496) or (438/499) or (438/496) or (438/508) or (438/508) or (438/509) or (438/514) or (438/787) or (438/788) CCLS. 34 ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and ((soi or (silicon near2 por grant)) near3 (substrate or wafer)) mear3 (substrate or sof or (silicon near2 por grant) near2 por grant) near2 quartz) or sof or (silicon near2 por grant) near2 quartz) or sof or (silicon near2 por grant) near3 (substrate or sof or (silicon near2 por grant) near3 (substrate or sof or (silicon near2 quartz) or sof or (silicon near2 por grant) near3 (substrate or sof or (silicon near2 quartz) or sof or (silicon near2 por grant) near3 (substrate or sof or (silicon near2 quartz) or sof or (silicon near2 quartz) or sof or (silicon near2 quartz) or sof or (silicon near2 quartz) or sof or (silicon near2 quartz) or sof or (silicon near2 quartz) or sof or (silicon near2 quartz) or sof or (silicon near2 quartz) or sof or (silicon near2 quartz) or sof or (silicon near3)) and (wafer near2 bond\$3) and ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and (wafer near2 bond\$3)) and (wafer near2 bond\$3)) and (wafer near2 bond\$3)) and (wafer near2 lamp) and (anneal\$3 or heat\$3) or heat\$3) and (((soi or wafer)) and (wafer near2 bond\$3)) and (wafer near2 bond\$4) and wafer | | | | | |
| near3 (substrate or wafer)) and ((((438/419) or (438/458) or (438/473) or (438/474) or (438/475) or (438/477) or (438/475) or (438/477) or (438/479) or (438/480) or (438/499) or (438/496) or (438/499) or (438/496) or (438/508) or (438/509) or (438/514) or (438/787) or (438/787) or (438/788)).CCLS.) - 34 ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and ((soi or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) - 10693 wafer near2 bond\$3 - 2450 (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) wafer near2 bond\$3) - 0 (((soi or (silicon near2 insulator) or soq or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) - 0 (((soi or (silicon near2 insulator) or soq or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) - 0 (((soi or (silicon near2 insulator) or soq or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3)) and ((((xe adj arc) near2 lamp) and (anneal\$3 bor heat\$3)) and ((((xe adj arc) near2 lamp) and (anneal\$3 bor heat\$3)) and ((((xe adj arc) near2 lamp) and (anneal\$3 bor heat\$3)) anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 poreign)) near3 (substrate or USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USP | | | | | |
| (((438/149) or (438/311) or (438/458) or (438/473) or (438/474) or (438/475) or (438/477) or (438/479) or (438/480) or (438/495) or (438/495) or (438/495) or (438/496) or (438/496) or (438/396) or (438/508) or (438/508) or (438/509) or (438/514) or (438/517) or (438/514) or (438/787) or (438/514) or (438/787) or (438/581).CLS.) - 34 ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and ((soi or (silicon near2 insulator) or soq or (silicon near2 foreign)) near3 (substrate or wafer)) - 10693 wafer near2 bond\$3 - 2450 ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) - 0 (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3)) and ((((soi or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3)) and ((((soi adj arc) near2 lamp) and (anneal\$3 or heat\$3))) - 3933068 anneal\$3 or heat\$3 - 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 insulator)) - 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 quartz) or sof or (silicon near2 puartz) or sof or (silicon near2 puartz) or soq or (silicon near2 puartz) or sof or (silicon near2 puartz) or sof or (silicon near2 puartz) or sof or (silicon near2 puartz) or sof or (silicon near2 puartz) or sof or (silicon near2 puartz) or sof or (silicon near2 puartz) or sof or (silicon near2 puartz) or sof or (silicon near2 puartz) or sof or (silicon near2 puartz) or sof or (silicon near2 puartz) or sof or (silicon near2 puartz) or sof or (silicon near2 puartz) or sof or (silicon near2 puartz) or sof or (silicon near2 puartz) or sof or (silicon near2 puartz) or sof or (silicon near2 puartz) or sof or (silicon near2 puartz) or sof or (silicon pear2 puartz) or sof or (silicon pear2 puartz) or sof or (silicon pear2 puartz) puarty puarty p | | | | · · | |
| (438/473) or (438/474) or (438/475) or (438/477) or (438/477) or (438/477) or (438/479) or (438/480) or (438/495) or (438/495) or (438/495) or (438/495) or (438/496) or (438/508) or (438/509) or (438/514) or (438/788).CCLS.) - 34 ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and ((soi or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) - 10693 wafer near2 bond\$3 USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USP | | | | 154 - 105 | |
| (438/477) or (438/496) or (438/490) or (438/495) or (438/496) or (438/496) or (438/496) or (438/508) or (438/508) or (438/509) or (438/508).octo.s) ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3))) and ((soi or (silicon near2 usrPGPUB; insulator) or soq or (silicon near2 foreign)) near3 (substrate or wafer)) and (soi or (silicon near2 foreign)) near3 (substrate or wafer) and (soi or (silicon near2 foreign)) near3 (substrate or wafer) and (wafer near2 bond\$3) and ((soi or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) and (((xe adj arc) near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) and (((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and (((soi or (silicon near2 lamp) and (anneal\$3 or heat\$3)) and (((soi or (silicon near2 lamp) and (anneal\$3 or heat\$3)) and (((soi or (silicon near2 lamp) and (anneal\$3 or heat\$3)) and (((soi or (silicon near2 lamp) and (anneal\$3 or heat\$3)) and (((soi or (silicon near2 lamp) and (anneal\$3 or heat\$3)) and (((soi or (silicon near2 lamp) and (anneal\$3 or heat\$3)) and (((soi or (silicon near2 lamp) and (anneal\$3 or heat\$3)) and (((soi or (silicon near2 lamp) and (anneal\$3 or heat\$3)) and (((soi or (silicon near2 lamp) and (anneal\$3 or heat\$3)) and (((soi or (silicon near2 lamp) and (anneal\$3 or heat\$3)) and ((soi or (silicon near2 lamp) and (anneal\$3 or heat\$3)) and ((soi or (silicon near2 lamp) and (anneal\$3 or heat\$3)) and ((soi or (silicon near2 lamp) and (anneal\$3 or heat\$3)) and ((soi or (silicon near2 lamp) and (anneal\$3 or heat\$3)) and ((soi or (silicon near2 lamp) and (anneal\$3)) and (substrate or (silicon near2 lamp)) near3 (substrate or (silicon near2 lamp)) near3 (substrate or (silicon near2 lamp)) near3 (substrate or (silicon near2 lamp)) near3 (substrate or (silicon near2 lamp)) near3 (substrate or (silicon near2 lamp)) near3 (substrate or (silicon near2 lamp)) near3 (substrate or (silicon near2 lamp)) near3 (substrate or (silicon near2 lamp)) near3 (substrate or (silicon near2 lamp)) near3 (substrate or (| | | | | |
| (438/495) or (438/508) or (438/499) or (438/406) or (438/508) or (438/509) or (438/514) or (438/508) or (438/509) or (438/514) or (438/788)).CCLS.) 34 ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and ((soi or (silicon near2 quartz) or sof or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IBM TDB USPAT; USPGUB; EPG; JPG; DERWENT; EPG; JPG; DERWENT; EPG; JPG; JPG; DERWENT; EPG; JPG; JPG; JPG; JPG; JPG; JPG; JPG; J | | | | | |
| (438/406) or (438/508) or (438/509) or (438/514) or (438/787) or (438/781) or (438/787) or (438/788)).CCLS.) (((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and (((soi or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer) and (wafer near2 bond\$3 - 2450 ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) - 0 (((soi or (silicon near2 insulator) or soq or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) - 0 (((soi or (silicon near2 insulator) or soq or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) and ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3))) anneal\$3 or heat\$3) - 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 foreign)) near3 (substrate or wafer); limm TDB (DERWENT; limm TDB) - 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 foreign)) near3 (substrate or DERWENT; limm TDB (DERWENT; limm TDB) - 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 foreign)) near3 (substrate or DERWENT; limm TDB) - 1808 (anneal\$3 or heat\$3) and ((soi or (silicon near2 insulator) or soq or (silicon near2 foreign)) near3 (substrate or DERWENT; limm TDB) - 1808 (anneal\$3 or heat\$3) and ((soi or (silicon near2 foreign)) near3 (substrate or DERWENT; limm TDB) - 1808 (anneal\$3 or heat\$3) and ((soi or (silicon near2 foreign)) near3 (substrate or DERWENT; limm TDB) - 1808 (anneal\$3 or heat\$3) and ((soi or (silicon near2 foreign)) near3 (substrate or DERWENT; limm TDB) | | | | | |
| - 438/514) or (438/787) or (438/788)).CCLS.) ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and ((soi or (silicon near2 upartz) or sof or (silicon near2 toreign)) near3 (substrate or wafer)) - 2450 ((soi or (silicon near2 insulator) or soq or (silicon near2 toreign)) near3 (substrate or wafer)) - 2450 ((soi or (silicon near2 insulator) or soq or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) - 0 (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) - 0 (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3)) and ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and (((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) - 3933068 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 foreign)) near3 (substrate or DERWENT; IBM_TDB - 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 foreign)) near3 (substrate or DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; | | | | | |
| 10693 (((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and ((soi or (silicon near2 quartz) or soq or (silicon near2 foreign)) near3 (substrate or wafer)) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; USPĀT US-PGPUB; U | | | | | |
| - 34 ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and ((soi or (silicon near2 insulator) or soq or (silicon near2 toreign)) near3 (substrate or wafer)) - 10693 | | | | | |
| or heat\$3)) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) - 10693 | - | 34 | | USPAT; | 2004/08/20 17:53 |
| insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) wafer near2 bond\$3 - 2450 ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer) and (wafer near2 bond\$3) - 0 ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) - 0 ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3)) and (((se adj arc) near2 lamp) and (anneal\$3 or heat\$3)) - 3933068 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or DERWENT; IBM_TDB 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or DERWENT; | | | | | |
| quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) wafer near2 bond\$3 - 2450 ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) - 0 (((soi or (silicon near2 insulator) or soq or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) - 0 (((soi or (silicon near2 insulator) or soq or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3)) and ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3))) anneal\$3 or heat\$3 - 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or 1808 (anneal\$3 or heat\$3) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or 1808 (anneal\$3 or heat\$3) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or 1808 (anneal\$3 or heat\$3) and ((soi or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (sil | | | | EPO; JPO; | |
| - 10693 wafer near2 bond\$3 - 2450 ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) - 0 (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) and (((soi or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3)) and (((soi or (silicon near2 lamp) and (anneal\$3 or heat\$3))) anneal\$3 or heat\$3)) anneal\$3 or heat\$3) - 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 lamp) and (substrate or DERWENT; IBM_TDB - 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 quartz) or sof or (silicon near2 procedus)) near3 (substrate or DERWENT; IBM_TDB) | | | quartz) or sof or (silicon near2 foreign)) | DERWENT; | |
| 2450 | | | | IBM TDB | |
| - 2450 ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or (silicon near2 quartz) or sof or (silicon near2 quartz) or sof or (silicon near2 quartz) or sof or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; | - | 10693 | wafer near2 bond\$3 | USPAT; | 2004/08/20 18:19 |
| - 2450 ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) - 0 (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3)) and ((((xe adj arc) near2 lamp) and (anneal\$3) or heat\$3))) - 3933068 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 insulator)) or soq or (silicon near2 quartz) or sof or (silicon near2 insulator)) - 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 quartz))) or soq or (silicon near2 quartz)) or sof or (silicon near2 quartz)) or sof or (silicon near2 quartz)) or sof or (silicon near2 quartz)) - 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 quartz)))) or sof or (silicon near2 quartz)) or sof or (silicon near2 quartz)) - 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 quartz)))) or sof or (silicon near2 quartz))) - 1808 (anneal\$3 or heat\$3) and ((soi or (silicon near2 quartz))) - 1808 (anneal\$3 or heat\$3) and ((soi or (silicon near2 quartz)))) - 1808 (anneal\$3 or heat\$3) and ((soi or (silicon near2 quartz)))) - 1808 (anneal\$3 or heat\$3) and ((soi or (silicon near2 quartz)))) - 1808 (anneal\$3 or heat\$3) and ((soi or (silicon near2 quartz))))) | | | | | |
| - 2450 ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) - 0 (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3)) and ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3))) - 3933068 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or DERWENT; | | | | , , | |
| - 2450 ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 pond\$3) - 0 (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 pond\$3)) and (((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and (((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3)) and (((soi or (silicon near2 insulator)) or soq or (silicon near2 insulator)) or soq or (silicon near2 quartz) or sof or (silicon pear2 foreign)) near3 (substrate or (silicon peawent; peo; JPO; near2 foreign)) near3 (substrate or (silicon peawent; peo; JPO; neawent; peo; JPO; neawent; peo; JPO; neawent; peo; JPO; neawent; peo; JPO; near2 foreign)) near3 (substrate or (silicon peawent; peo; JPO; neawent; p | | | | | |
| or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) O (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or us-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; IBM_ | | | | | 0004405455 |
| (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3) (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3)) and (((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3))) 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or DERWENT; | - | 2450 | | | 2004/08/20 18:02 |
| or wafer)) and (wafer near2 bond\$3) (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or uspective or wafer)) and (wafer near2 bond\$3)) and (((xe adj arc) near2 lamp) and (anneal\$3 to heat\$3))) 3933068 anneal\$3 or heat\$3 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or to the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the content of the cont | | | | · · | |
| - 0 (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or use property or wafer)) and (wafer near2 bond\$3)) and (((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3))) - 3933068 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or use property insulator) or soq or (silicon near2 foreign)) near3 (substrate or use property insulator) or soq or (part) property insulator) or soq or (silicon near2 quartz) or sof or (silicon perceive) property insulator) or soq or (silicon near2 quartz) or sof or (silicon perceive) property insulator) or soq or (silicon near2 quartz) or sof or (silicon perceive) property insulator) prop | | | (Silicon nearz foreign)) near3 (Substrate | | |
| - (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or ()((xe adj arc) near2 lamp) and (anneal\$3 (substrate) or heat\$3)) and (((xe adj arc) near2 lamp) and (anneal\$3 (substrate) or heat\$3)) and (((xe adj arc) near2 lamp) and (anneal\$3 (substrate) or heat\$3)) and (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or (silicon perwent; left) definition (silicon near2 quartz) or sof or (silicon perwent; left) definition (silicon near2 quartz) or sof or (silicon perwent; left) definition (silicon near2 quartz) or sof or (silicon perwent; left) definition (silicon near2 quartz) or sof or (silicon perwent; left) definition (silicon perwent) definition (sili | | | or waier)) and (waier near2 bond\$3) | | |
| or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate or (silicon near2 foreign)) near3 (substrate near2 foreign) near3 (substrate near2 f | _ | | ///goi or /giligon noord inculator\ | | 2004/00/20 10:00 |
| <pre>(silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond\$3)) and ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3))) anneal\$3 or heat\$3 - 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 foreign)) near3 (substrate or</pre> EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; DERWENT; DERWENT; DERWENT; DERWENT; | - | | | | 2004/08/20 18:02 |
| or wafer)) and (wafer near2 bond\$3)) and ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3))) anneal\$3 or heat\$3 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or DERWENT; | ļ | | | | |
| ((((xe adj arc) near2 lamp) and (anneal\$3 or heat\$3))) anneal\$3 or heat\$3 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or DERWENT; |] | | | r e | |
| or heat\$3))) anneal\$3 or heat\$3 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; US-PGPUB; EPO; JPO; DERWENT; USPAT; USPAT; US-PGPUB; USPAT; US-PGPUB; (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or DERWENT; | | | | | |
| - 3933068 anneal\$3 or heat\$3 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; DERWENT; | | | | 1011_100 | |
| - 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or (US-PGPUB; EPO; JPO; near2 foreign)) near3 (substrate or (US-PGPUB; EPO; JPO; near2 foreign)) near3 (substrate or (US-PGPUB; EPO; JPO; near2 foreign)) near3 (substrate or (US-PGPUB; EPO; JPO; near2 foreign)) near3 (substrate or (US-PGPUB; EPO; JPO; near2 foreign)) | _ | 3933068 | | USPAT: | 2004/08/20 18:55 |
| - 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or DERWENT; | | 0223330 | | | |
| - 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or DERWENT; | | | | | |
| - 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or DERWENT; | l i | | | · · | |
| - 1808 (anneal\$3 or heat\$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or DERWENT; | | | | | |
| (silicon near2 insulator) or soq or US-PGPUB; (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or DERWENT; | _ | 1808 | (anneal\$3 or heat\$3) and (((soi or | | 2004/08/20 18:05 |
| (silicon near2 quartz) or sof or (silicon EPO; JPO; near2 foreign)) near3 (substrate or DERWENT; | | | · · · · · · · · · · · · · · · · · · · | | , == |
| near2 foreign)) near3 (substrate or DERWENT; | | | | | |
| wafer)) and (wafer near2 bond\$3)) TRM TDR | | | near2 foreign)) near3 (substrate or | DERWENT; | |
| | | | <pre>wafer)) and (wafer near2 bond\$3))</pre> | IBM_TDB | |

| | | | (====== | 1 000 1 100 100 100 00 |
|---|----------|-------------------------------------------------------------------------------------|------------------------|------------------------|
| - | 281 | ((xe adj arc) near2 lamp) | USPAT; US-PGPUB; | 2004/08/20 18:03 |
| • | | | EPO; JPO; | |
| | | | DERWENT; | |
| _ | 0 | ((anneal\$3 or heat\$3) and (((soi or | IBM_TDB USPAT; | 2004/08/20 18:04 |
| | | (silicon near2 insulator) or soq or | US-PGPUB; | 2004/00/20 10:01 |
| | | (silicon near2 quartz) or sof or (silicon | EPO; JPO; | |
| | | near2 foreign)) near3 (substrate or | DERWENT; | |
| | | <pre>wafer)) and (wafer near2 bond\$3))) and (((xe adi arc) near2 lamp))</pre> | IBM_TDB | |
| _ | 40 | | USPAT; | 2004/08/20 18:29 |
| 1 | | (silicon near2 insulator) or soq or | US-PGPUB; | |
| | | (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or | EPO; JPO; DERWENT; | |
| | | wafer)) and (wafer near2 bond\$3))) and | IBM TDB | |
| | | (lamp near5 intensit\$3) | - | |
| - | 15436 | wafer near5 bond\$3 | USPAT; | 2004/08/20 18:20 |
| | | | US-PGPUB; EPO; JPO; | |
| | | | DERWENT; | |
| | 0.505 | | IBM_TDB | |
| - | 8537 | (wafer near5 bond\$3) and (anneal\$3 or heat\$3) | USPAT; US-PGPUB; | 2004/08/20 18:20 |
| | | neacy3) | EPO; JPO; | |
| | | | DERWENT; | |
| | 1232 | implanté mague (huduagan magu iané) | IBM_TDB USPAT; | 2004/08/20 18:27 |
| - | 1232 | implant\$ near5 (hydrogen near ion\$1) | US-PGPUB; | 2004/08/20 18:27 |
| | j | | EPO; JPO; | |
| | | | DERWENT; | |
| _ | 179 | (wafer near5 bond\$3) same (implant\$ near5 | IBM_TDB USPAT; | 2004/08/20 18:57 |
| | 1/9 | (hydrogen near ion\$1)) | US-PGPUB; | 2004/00/20 10.5/ |
| | | | EPO; JPO; | |
| | | | DERWENT; IBM TDB | |
| _ | 162 | ((wafer near5 bond\$3) same (implant\$ near5 | USPAT; | 2004/08/20 18:28 |
| | | (hydrogen near ion\$1))) and ((soi or | US-PGPUB; | |
| | | (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon | EPO; JPO; DERWENT; | |
| | | near2 foreign)) near3 (substrate or | IBM_TDB | |
| | | wafer)) | · - · | |
| _ | 158 | (((wafer near5 bond\$3) same (implant\$ near5 (hydrogen near ion\$1))) and ((soi or | USPAT; US-PGPUB; | 2004/08/20 18:28 |
| | | (silicon near2 insulator) or soq or | EPO; JPO; | |
| | | (silicon near2 quartz) or sof or (silicon | DERWENT; | |
| | | near2 foreign)) near3 (substrate or wafer))) and (anneal\$3 or heat\$3) | IBM_TDB | |
| _ | 2 | ((((wafer near5 bond\$3) same (implant\$ | USPAT; | 2004/08/20 19:38 |
| | | near5 (hydrogen near ion\$1))) and ((soi or | US-PGPUB; | |
| | | (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon | EPO; JPO; DERWENT; | |
| | | near2 foreign)) near3 (substrate or | IBM TDB | |
| | | wafer))) and (anneal\$3 or heat\$3)) and | _ | |
| _ | 37 | <pre>(lamp near5 intensit\$3) ((((wafer near5 bond\$3) same (implant\$</pre> | USPAT; | 2004/08/20 18:31 |
| | | near5 (hydrogen near ion\$1))) and ((soi or | US-PGPUB; | 2003/00/20 10:31 |
| | | (silicon near2 insulator) or soq or | EPO; JPO; | |
| | | (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or | DERWENT; | |
| | | wafer))) and (anneal\$3 or heat\$3)) and | IBM_TDB | |
| | | lamp | | |
| - | 366 | <pre>(wafer near5 bond\$3) and (implant\$ near5 (hydrogen near ion\$1))</pre> | USPAT; | 2004/08/20 18:58 |
| | | (wydrogen near rongr)) | US-PGPUB; EPO; JPO; | |
| | | | DERWENT; | |
| | <u> </u> | | IBM TDB | |

| | | | , | |
|--------------|------|--------------------------------------------------------------------------------------|------------------------|------------------|
| - | 310 | ((wafer near5 bond\$3) and (implant\$ near5 | USPAT; | 2004/08/20 18:58 |
| | | (hydrogen near ion\$1))) and ((soi or | US-PGPUB; | |
| | | (silicon near2 insulator) or soq or | EPO; JPO; | |
| | | (silicon near2 quartz) or sof or (silicon | DERWENT; | |
| | | <pre>near2 foreign)) near3 (substrate or wafer))</pre> | IBM_TDB | |
| | ٥ ا | I | USPAT; | 2004/08/20 18:59 |
| - | | (hydrogen near ion\$1))) and (soi or | US-PGPUB; | 2004/08/20 18.39 |
| | | (silicon near2 insulator) or soq or | EPO; JPO; | |
| | | (silicon near2 quartz) or sof or (silicon | DERWENT; | |
| | | near2 foreign)) near3 (substrate or | IBM TDB | |
| | | wafer))) and (((anneal\$3 or heat\$3) same | _ | |
| | | lamp) near5 (support near2 substrate)) | | İ |
| - | 0 | | USPAT; | 2004/08/20 18:59 |
| | | (hydrogen near ion\$1))) and (((anneal\$3 or | US-PGPUB; | |
| | | heat\$3) same lamp) near5 (support near2 | EPO; JPO; | |
| | | substrate)) | DERWENT; | |
| | 0 | /// | IBM_TDB USPAT; | 2004/08/20 18:59 |
| - | " | (((anneal\$3 or heat\$3) same lamp) near5 (support near2 substrate)) and ((soi or | US-PGPUB; | 2004/08/20 18:59 |
| | | (silicon near2 insulator) or sog or | EPO; JPO; | |
| | | (silicon near2 quartz) or sof or (silicon | DERWENT; | |
| | | near2 foreign)) near3 (substrate or | IBM TDB | ! |
| | | wafer)) | | i |
| - | 43 | ((anneal\$3 or heat\$3) same lamp) near5 | USPAT; | 2004/08/20 19:01 |
| | | (support near2 substrate) | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | 0015 | | IBM_TDB | 0004/00/00 10 11 |
| - | 2013 | (anneal\$3 or heat\$3) near3 (support near2 | USPAT; | 2004/08/20 19:02 |
| | | substrate) | US-PGPUB; | |
| | | | EPO; JPO; DERWENT; | |
| | | | IBM TDB | |
| _ | 71 | ((anneal\$3 or heat\$3) near3 (support near2 | USPAT; | 2004/08/20 19:02 |
| | , | substrate)) and ((soi or (silicon near2 | US-PGPUB; | 2001,00,20 13.02 |
| | | insulator) or soq or (silicon near2 | EPO; JPO; | |
| | | quartz) or sof or (silicon near2 foreign)) | DERWENT; | |
| | | near3 (substrate or wafer)) | IBM_TDB | |
| - | 16 | | USPAT; | 2004/08/20 19:03 |
| ļ | | near2 substrate)) and ((soi or (silicon | US-PGPUB; | |
| | | near2 insulator) or soq or (silicon near2 | EPO; JPO; | |
| | | quartz) or sof or (silicon near2 foreign)) | DERWENT; | |
| | | near3 (substrate or wafer))) and (implant\$ near5 (hydrogen near ion\$1)) | IBM_TDB | |
| _ | 1 | "5543636".PN. | USPAT | 2004/08/20 19:22 |
| - | 4 | ("5854123" "5882987" "5953622" | USPAT | 2004/08/20 19:23 |
| | | "6010579").PN. | | |
| - | 6 | | USPAT | 2004/08/20 19:24 |
| | | "6251754" "6294814" "6323108").PN. | | |
|] - | 1 | ("6376806").PN. | USPAT | 2004/08/20 19:35 |
|] - | 15 | ("4356384" "4436985" "4707217" | USPAT | 2004/08/20 19:36 |
| | | "4755654" "5073698" "5577157" | | |
| | | "5722761" "5756369" "5811327" "5840118" "5892332" "5893952" | | |
|] | | "5840118" "5892332" "5893952" "5937282" "6080965" "6144171").PN. | | |
| _ | 335 | | USPAT; | 2004/08/20 19:52 |
| | 333 | LICON HOULE GIMOULYS | US-PGPUB; | 2004/00/20 19.32 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
|] | | | IBM TDB | |
| j - | 0 | (flash near2 anneal\$3) near5 (support | USPAT; | 2004/08/20 19:40 |
| | İ | near2 substrate) | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| [| 4 | /flach noam2 name=162\ mas=16 / | IBM_TDB | 2004/00/00 10 10 |
| ⁻ | 1 | <pre>(flash near2 anneal\$3) near10 (support near2 substrate)</pre> | USPAT; | 2004/08/20 19:40 |
| | | nearz substrate; | US-PGPUB; EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM TDB | |
| <u> </u> | | | | |

Page 4

| - | 1 | (flash near2 anneal\$3) same (support near2 | USPAT; | 2004/08/20 19:40 |
|---|----------|---------------------------------------------|-----------------------|--------------------|
| | | substrate) | US-PGPUB; | |
| | 1 | | EPO; JPO; DERWENT; | |
| | ŀ | | IBM TDB | |
| _ | 7 | (flash near2 anneal\$3) and (support near2 | USPAT; | 2004/08/20 19:44 |
| | ' | substrate) | US-PGPUB; | 2001, 00, 20 13111 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM_TDB | |
| - | 0 | (flash near2 anneal\$3) near5 (separt\$5 | USPAT; | 2004/08/20 19:45 |
| | | same substrate) | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| _ | 0 | (flash near2 anneal\$3) near5 separt\$5 | IBM_TDB USPAT; | 2004/08/20 19:45 |
| | " | (Trash hearz annears) hears separces | US-PGPUB; | 2004/08/20 19:43 |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | | | IBM TDB | |
| _ | 0 | (flash near2 anneal\$3) near10 separt\$5 | USPĀT; | 2004/08/20 19:46 |
| | | - | US-PGPUB; | |
| | | | EPO; JPO; | |
| 1 | | | DERWENT; | |
| | | (61-2) 100: | IBM_TDB | 0004/00/00 10 := |
| - | 2 | , , , , , , , , , , , , , , , , , , , , | USPAT; | 2004/08/20 19:47 |
| | İ | near5 substrate) | US-PGPUB; | |
| | | | EPO; JPO; DERWENT; | |
| | | | IBM TDB | |
| - | 1 | (flash near2 anneal\$3) near10 (through | USPAT; | 2004/08/20 19:48 |
| | _ | near2 substrate) | US-PGPUB; | |
| | | · | EPO; JPO; | |
| | 1 | | DERWENT; | |
| | | | IBM_TDB | |
| - | 1 | (flash near2 anneal\$3) near10 (through | USPAT; | 2004/08/20 19:48 |
| | | same substrate) | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; IBM TDB | |
| _ | 27 | (flash near2 anneal\$3) near10 (substrate) | USPAT; | 2004/08/20 19:50 |
| | | | US-PGPUB; | |
| | | | EPO; JPO; | |
| | | | DERWENT; | |
| | 1 . | | IBM_TDB | |
| - | 1 | (' ::-u u::::uaryo, oumo (::]uroyo:: | USPAT; | 2004/08/21 16:29 |
| 1 | 1 | near2 ion\$1) | US-PGPUB; | |
| | 1 | | EPO; JPO; DERWENT; | |
| 1 | 1 | | IBM TDB | |
| - | 18 | flash near2 anneal\$3 and ((soi or (silicon | USPAT; | 2004/08/20 19:55 |
| | | near2 insulator) or soq or (silicon near2 | US-PGPUB; | |
| | | quartz) or sof or (silicon near2 foreign)) | EPO; JPO; | |
| | | near3 (substrate or wafer)) | DERWENT; | |
| 1 | 40016 | 61-2h | IBM_TDB | 0004/00/05 |
| - | 42016 | | USPAT; | 2004/08/21 18:41 |
| | 1 | near2 lamp) or xenon | US-PGPUB; | |
| | | | EPO; JPO; DERWENT; | |
| | | | IBM TDB | |
| _ | 20 | (flash near2 anneal\$3 or ((xe adj arc) | USPAT; | 2004/08/20 19:56 |
| | | near2 lamp) or xenon) same ((soi or | US-PGPUB; | |
| | 1 | (silicon near2 insulator) or soq or | EPO; JPO; | |
| | | (silicon near2 quartz) or sof or (silicon | DERWENT; | ! |
| | | near2 foreign)) near3 (substrate or | IBM_TDB | |
| _ | 41728 | wafer)) | tion. | 2004/00/01 16 55 |
| " | 41/28 | ((xe adj arc) near2 lamp) or xenon | USPAT; US-PGPUB; | 2004/08/21 16:30 |
| | | | EPO; JPO; | |
| | | , | DERWENT; | |
| | | | IBM TDB | |
| | | | | |

| _ | 40914 | (soi or (silicon near2 insulator) or soq | USPAT; | 2004/08/21 | 16:28 |
|---|-------|--------------------------------------------|-----------|------------|-------|
| | | or (silicon near2 quartz) or sof or | US-PGPUB; | | |
| | | (silicon near2 foreign)) | EPO; JPO; | | i |
| | | | DERWENT; | | |
| | | | IBM_TDB | | |
| _ | 869 | (((xe adj arc) near2 lamp) or xenon) and | USPAT; | 2004/08/21 | 16:28 |
| | | ((soi or (silicon near2 insulator) or soq | US-PGPUB; | | |
| | | or (silicon near2 quartz) or sof or | EPO; JPO; | | |
| | | (silicon near2 foreign))) | DERWENT; | | |
| | | | IBM TDB | | |
| _ | 1422 | (hydrogen near2 ion\$1) near5 implant\$5 | USPĀT; | 2004/08/21 | 16:29 |
| | | | US-PGPUB; | | |
| | | | EPO; JPO; | | |
| | | | DERWENT; | | |
| | | | IBM TDB | | |
| - | 47 | ((((xe adj arc) near2 lamp) or xenon) and | USPAT; | 2004/08/21 | 16:29 |
| | | ((soi or (silicon near2 insulator) or sog | US-PGPUB; | | |
| | | or (silicon near2 quartz) or sof or | EPO; JPO; | | |
| | | (silicon near2 foreign)))) and (| DERWENT; | | ļ |
| | | (hydrogen near2 ion\$1) near5 implant\$5) | IBM TDB | | |
| _ | 19527 | ((xe adj arc) near2 lamp) or xenon near3 | USPĀT; | 2004/08/21 | 16:30 |
| | | lamp | US-PGPUB; | | |
| | | | EPO; JPO; | | 1 |
| | | | DERWENT; | | F |
| | l | | IBM TDB | | ļ |
| _ | 330 | (((xe adj arc) near2 lamp) or xenon near3 | USPAT; | 2004/08/21 | 16:30 |
| | | lamp) and ((soi or (silicon near2 | US-PGPUB; | | |
| | | insulator) or soq or (silicon near2 | EPO; JPO; | | |
| | | quartz) or sof or (silicon near2 foreign)) | DERWENT; | | |
| | |) | IBM TDB | | |
| _ | 13 | ((((xe adj arc) near2 lamp) or xenon | USPAT; | 2004/08/21 | 16:31 |
| | | near3 lamp) and ((soi or (silicon near2 | US-PGPUB; | -001,00,22 | |
| | | insulator) or soq or (silicon near2 | EPO; JPO; | | - 1 |
| | | quartz) or sof or (silicon near2 foreign)) | DERWENT; | | 1 |
| | |)) and ((hydrogen near2 ion\$1) near5 | IBM TDB | | |
| | | implant\$5) | ~~ | | |
| _ | 35 | | USPAT; | 2004/08/21 | 20:53 |
| | | wafer) | US-PGPUB; | 2001,00,21 | 20.00 |
| | | | EPO; JPO; | | ľ |
| | 1 | | DERWENT; | | ŀ |
| | | | IBM TDB | | |